# Electronics Semester 5

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# Contents

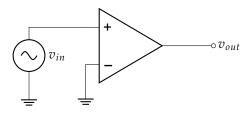
Chapter 1	Amplifiers	Page 2
1.1	Gain of Amplifiers	2
1.2	Equivalent Circuit of an Amplifier	2
1.3	Cascade Amplifiers	3
Chapter 2	Diodes	Page 4
2.1	The Ideal Diode	4
	Simple Application: The Half-Wave Rectifier — $4$	
2.2	Terminal Characteristics of Junction Diodes	5
2.3	The Forward Bias Region	5
Chapter 3	MOSFETs	Page 6
3.1	MOSFET Modes of Operation	6
	Cut-off — 6 • Triode — 6 • Saturation — 6	

## Chapter 1

## **Amplifiers**

#### 1.1 Gain of Amplifiers

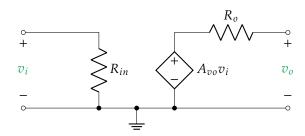
$$\begin{aligned} \text{Voltage Gain} &= \frac{v_{out}}{v_{in}} \\ \text{Current Gain} &= \frac{i_{out}}{i_{in}} \\ \text{Power Gain} &= \frac{P_{out}}{P_{in}} \end{aligned}$$



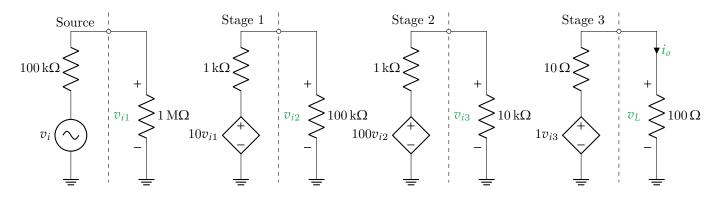
In decibels, the gain is given by

$$\begin{aligned} & \text{Voltage Gain} = 20 \log \left( \frac{v_{out}}{v_{in}} \right) \\ & \text{Current Gain} = 20 \log \left( \frac{i_{out}}{i_{in}} \right) \\ & \text{Power Gain} = 10 \log \left( \frac{P_{out}}{P_{in}} \right) \end{aligned}$$

### 1.2 Equivalent Circuit of an Amplifier



### 1.3 Cascade Amplifiers



In the above circuit, the output voltage is given by

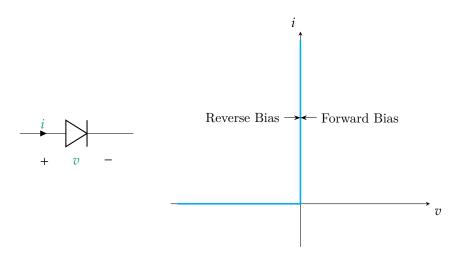
$$\begin{split} v_L &= 10 \cdot \frac{1 \, \mathrm{M}\Omega}{1 \, \mathrm{M}\Omega + 100 \, \mathrm{k}\Omega} \cdot 100 \cdot \frac{100 \, \mathrm{k}\Omega}{100 \, \mathrm{k}\Omega + 1 \, \mathrm{k}\Omega} \cdot 1 \cdot \frac{10 \, \mathrm{k}\Omega}{10 \, \mathrm{k}\Omega + 1 \, \mathrm{k}\Omega} \cdot \frac{100 \, \Omega}{100 \, \Omega + 10 \, \Omega} \cdot v_i. \\ A_v &= \frac{v_L}{v_i} = 743.876 \, \mathrm{V/V}. \end{split}$$

## Chapter 2

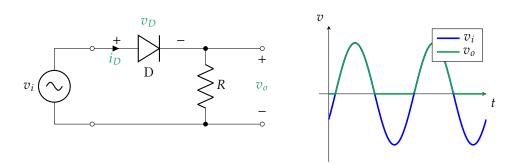
## Diodes

#### 2.1 The Ideal Diode

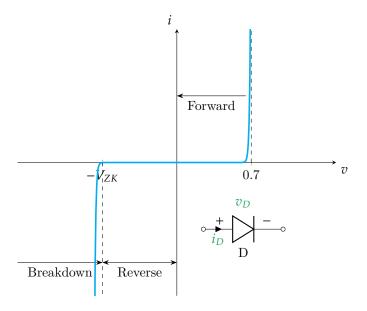
The ideal diode is a two terminal device that allows current to flow in one direction only.



#### 2.1.1 Simple Application: The Half-Wave Rectifier



#### 2.2 Terminal Characteristics of Junction Diodes



The characteristic curve of a diode consists of three regions:

- 1. The forward bias region, where the diode conducts current.  $v_D > 0$ .
- 2. The reverse bias region, where the diode blocks current.  $v_D < 0$ .
- 3. The breakdown region, where the diode conducts current in the reverse direction.  $v_D < -V_{ZK}$ .

#### 2.3 The Forward Bias Region

In the forward bias region, the diode conducts current. The current is given by

$$i = I_S \left( e^{\frac{v}{V_T}} - 1 \right).$$

Where  $I_S$  is the reverse saturation current, and  $V_T \approx 25\,\mathrm{mV}$  is the thermal voltage.

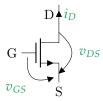
### Chapter 3

## **MOSFETs**

A MOSFET is a Metal Oxide Semiconductor Field Effect Transistor. It is a voltage controlled device. It has three terminals: the gate, the source, and the drain.



#### 3.1 MOSFET Modes of Operation



#### 3.1.1 Cut-off

In this mode, the MOSFET is off  $(i_D = 0)$ . The MOSFET is in cut-off when  $v_{GS} \leq V_{th}$ . Where  $V_{th}$  is the threshold voltage of the MOSFET.

#### **3.1.2** Triode

In this mode, the MOSFET is on  $(i_D \neq 0)$ . The MOSFET conducts current from the drain to the source. The MOSFET is in triode when  $v_{GS} > V_{th}$  and  $v_{DS} < v_{GS} - V_{th}$ .

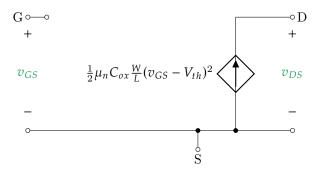
$$i_D = \mu_n C_{ox} \frac{W}{L} \left[ (v_{GS} - V_{th}) v_{DS} - \frac{v_{DS}^2}{2} \right].$$

#### 3.1.3 Saturation

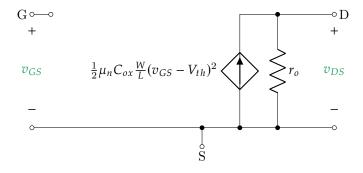
In this mode, the MOSFET is on  $(i_D \neq 0)$ . The MOSFET conducts current from the drain to the source. The MOSFET is in saturation when  $v_{GS} > V_{th}$  and  $v_{DS} > v_{GS} - V_{th}$ .

$$i_D = \frac{1}{2} \mu_n C_{ox} \frac{W}{L} (v_{GS} - V_{th})^2. \label{eq:ideal}$$

The large signal model of a MOSFET in saturation is as follows:



Accounting for the early effect.



$$r_o = \frac{V_A}{I_D} = \frac{1}{\lambda I_D}.$$